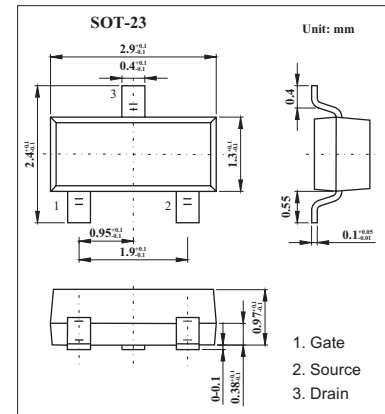
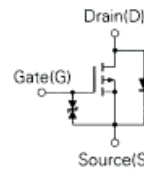


MOS Field Effect Transistor

2SJ461

■ Features

- Can be driven by a 2.5V power source.
- Not necessary to consider driving current because of its high input impedance.
- Possible to reduce the number of parts by omitting the bias resistor.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V _{DSS}	-50	V
Gate to source voltage	V _{GSS}	±7.0	V
Drain current (DC)	I _D	±0.1	A
Drain current(pulse) *	I _D	±0.2	A
Power dissipation	P _D	200	mW
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 μs; d ≤ 1%.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain to source breakdown voltage	V _{DSS}	I _D =-10mA, V _{GS} =0	-20			V
Gate to source breakdown voltage	V _{GSS}	I _G =±200 μA, V _{DS} =0	±10			V
Drain cut-off current	I _{DSS}	V _{DS} =-50V, V _{GS} =0			-100	μA
Gate leakage current	I _{GSS}	V _{GS} =±7.0V, V _{DS} =0			±10	μA
Gate to source cutoff voltage	V _{GS(off)}	V _{DS} =-3.0V, I _D =-1 μA	-0.7	-0.9	-1.3	V
Forward transfer admittance	Y _{fs}	V _{DS} =-3.0V, I _D =-10mA	12			ms
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =-2.5V, I _D =-3mA		46	100	Ω
		V _{GS} =-4.0V, I _D =-10mA		31	50	Ω
Input capacitance	C _{iss}	V _{DS} =-3.0V, V _{GS} =0, f=1MHZ		6		pF
Output capacitance	C _{oss}			9		pF
Reverse transfer capacitance	C _{rss}			1.6		pF
Turn-on delay time	t _{d(on)}			32		ns
Rise time	t _r	V _{DD} =-3.0V, V _{GS(on)} =-3.0V, I _D =-20mA R _L =200 Ω, R _G =10 Ω		270		ns
Turn-off delay time	t _{d(off)}			45		ns
Fall time	t _f			130		ns